SSTU32864

1.8 V configurable registered buffer for DDR2 RDIMM applications

Rev. 02 — 22 October 2004

Product data sheet



The SSTU32864 is a 25-bit 1:1 or 14-bit 1:2 configurable registered buffer designed for 1.7 V to 1.9 V V_{DD} operation.

All clock and data inputs are compatible with the JEDEC standard for SSTL_18. The control inputs are LVCMOS. All outputs are 1.8 V CMOS drivers that have been optimized to drive the DDR2 DIMM load.

The SSTU32864 operates from a differential clock (CK and \overline{CK}). Data are registered at the crossing of CK going HIGH, and \overline{CK} going LOW.

The C0 input controls the pinout configuration of the 1:2 pinout from A configuration (when LOW) to B configuration (when HIGH). The C1 input controls the pinout configuration from 25-bit 1:1 (when LOW) to 14-bit 1:2 (when HIGH).

The device supports low-power standby operation. When the reset input (\overline{RESET}) is LOW, the differential input receivers are disabled, and undriven (floating) data, clock and reference voltage (V_{REF}) inputs are allowed. In addition, when \overline{RESET} is LOW all registers are reset, and all outputs are forced LOW. The LVCMOS \overline{RESET} and Cn inputs must always be held at a valid logic HIGH or LOW level.

To ensure defined outputs from the register before a stable clock has been supplied, RESET must be held in the LOW state during power-up.

In the DDR2 RDIMM application, $\overline{\text{RESET}}$ is specified to be completely asynchronous with respect to CK and $\overline{\text{CK}}$. Therefore, no timing relationship can be guaranteed between the two. When entering reset, the register will be cleared and the data outputs will be driven LOW quickly, relative to the time to disable the differential input receivers. However, when coming out of reset, the register will become active quickly, relative to the time to enable the differential input receivers. As long as the data inputs are LOW, and the clock is stable during the time from the LOW-to-HIGH transition of $\overline{\text{RESET}}$ until the input receivers are fully enabled, the design of the SSTU32864 must ensure that the outputs will remain LOW, thus ensuring no glitches on the output.

The device monitors both DCS and CSR inputs and will gate the Qn outputs from changing states when both DCS and CSR inputs are HIGH. If either DCS or CSR input is LOW, the Qn outputs will function normally. The RESET input has priority over the DCS and CSR control and will force the outputs LOW. If the DCS-control functionality is not desired, then the CSR input can be hardwired to ground, in which case the setup time requirement for DCS would be the same as for the other Dn data inputs.

The SSTU32864 is available in a 96-ball, low profile fine-pitch ball grid array (LFBGA96) package.



2. Features

- Configurable register supporting DDR2 Registered DIMM applications
- Configurable to 25-bit 1:1 mode or 14-bit 1:2 mode
- Controlled output impedance drivers enable optimal signal integrity and speed
- Exceeds JESD82-7 speed performance (1.8 ns max. single-bit switching propagation delay; 2.0 ns max. mass-switching)

1.8 V configurable registered buffer for DDR2 RDIMM applications

- Supports up to 450 MHz clock frequency of operation
- Optimized pinout for high-density DDR2 module design
- Chip-selects minimize power consumption by gating data outputs from changing state
- Supports SSTL_18 data inputs
- Differential clock (CK and CK) inputs
- Supports LVCMOS switching levels on the control and RESET inputs
- Single 1.8 V supply operation
- Available in 96-ball, 13.5 × 5.5 mm, 0.8 mm ball pitch LFBGA package

3. Ordering information

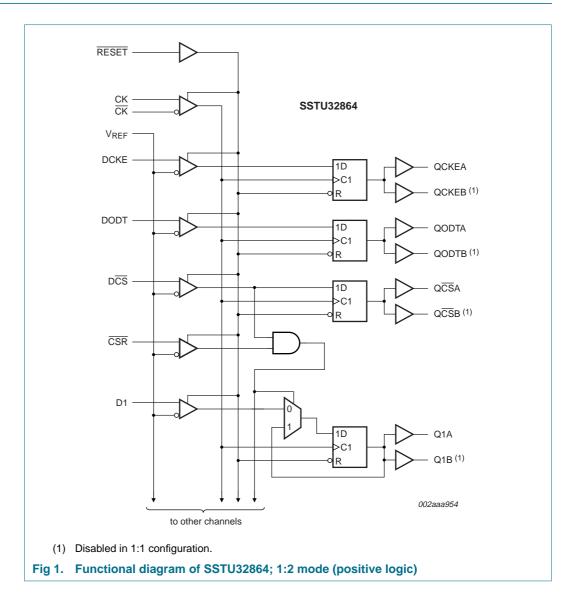
Table 1: Ordering information

 $T_{amb} = 0 \,^{\circ}C$ to +70 $^{\circ}C$.

Type number	Solder process	Package	Package					
		Name	Description	Version				
SSTU32864EC/G	Pb-free (SnAgCu solder ball compound)	LFBGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body $13.5 \times 5.5 \times 1.05$ mm	SOT536-1				
SSTU32864EC	SnPb solder ball compound	LFBGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body $13.5 \times 5.5 \times 1.05$ mm	SOT536-1				

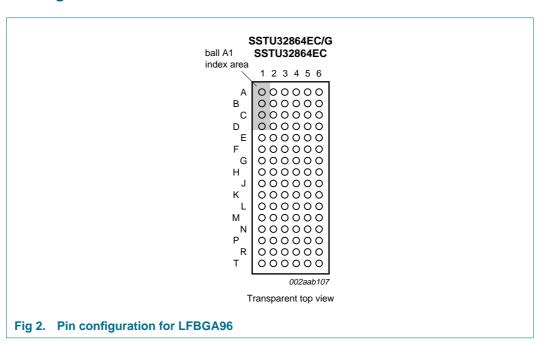


4. Functional diagram



5. Pinning information

5.1 Pinning

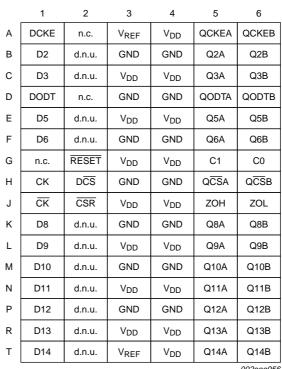


	1	2	3	4	5	6
А	DCKE	n.c.	V_{REF}	V_{DD}	QCKE	d.n.u.
В	D2	D15	GND	GND	Q2	Q15
С	D3	D16	V _{DD}	V _{DD}	Q3	Q16
D	DODT	n.c.	GND	GND	QODT	d.n.u.
E	D5	D17	V_{DD}	V _{DD}	Q5	Q17
F	D6	D18	GND	GND	Q6	Q18
G	n.c.	RESET	V_{DD}	V _{DD}	C1	C0
Н	СК	DCS	GND	GND	QCS	d.n.u.
J	СК	CSR	V _{DD}	V _{DD}	ZOH	ZOL
K	D8	D19	GND	GND	Q8	Q19
L	D9	D20	V_{DD}	V _{DD}	Q9	Q20
M	D10	D21	GND	GND	Q10	Q21
N	D11	D22	V_{DD}	V _{DD}	Q11	Q22
Р	D12	D23	GND	GND	Q12	Q23
R	D13	D24	V_{DD}	V_{DD}	Q13	Q24
Т	D14	D25	V _{REF}	V _{DD}	Q14	Q25
		•		•	•	002aaa955

Fig 3. Ball mapping; 1:1 register (C0 = 0, C1 = 0); top view

SSTU32864 **Philips Semiconductors**

1.8 V configurable registered buffer for DDR2 RDIMM applications



002aaa956

Fig 4. Ball mapping; 1:2 register A (C0 = 0, C1 = 1); top view

	1	2	3	4	5	6
Α	D1	n.c.	V _{REF}	V _{DD}	Q1A	Q1B
В	D2	d.n.u.	GND	GND	Q2A	Q2B
С	D3	d.n.u.	V _{DD}	V _{DD}	Q3A	Q3B
D	D4	n.c.	GND	GND	Q4A	Q4B
Е	D5	d.n.u.	V _{DD}	V _{DD}	Q5A	Q5B
F	D6	d.n.u.	GND	GND	Q6A	Q6B
G	n.c.	RESET	V _{DD}	V _{DD}	C1	C0
Н	СК	DCS	GND	GND	QCSA	QCSB
J	СK	CSR	V _{DD}	V _{DD}	ZOH	ZOL
K	D8	d.n.u.	GND	GND	Q8A	Q8B
L	D9	d.n.u.	V_{DD}	V _{DD}	Q9A	Q9B
М	D10	d.n.u.	GND	GND	Q10A	Q10B
Ν	DODT	d.n.u.	V_{DD}	V_{DD}	QODTA	QODTB
Р	D12	d.n.u.	GND	GND	Q12A	Q12B
R	D13	d.n.u.	V_{DD}	V_{DD}	Q13A	Q13B
Т	DCKE	d.n.u.	V _{REF}	V_{DD}	QCKEA	QCKEB

002aaa957

Fig 5. Ball mapping; 1:2 register B (C0 = 1, C1 = 1); top view

5.2 Pin description

Table 2: Pin description

Table 2: Pin o	description		
Symbol	Pin	Туре	Description
GND	B3, B4, D3, D4, F3, F4, H3, H4, K3, K4, M3, M4, P3, P4	ground input	ground
V_{DD}	A4, C3, C4, E3, E4, G3, G4, J3, J4, L3, L4, N3, N4, R3, R4, T4	1.8 V nominal	power supply voltage
V_{REF}	A3, T3	0.9 V nominal	input reference voltage
ZOH	J5	input	reserved for future use
ZOL	J6	input	reserved for future use
CK	H1	differential input	positive master clock input
CK	J1	differential input	negative master clock input
C0, C1	G6, G5	LVCMOS inputs	configuration control inputs
RESET	G2	LVCMOS input	Asynchronous reset input. Resets registers and disables V_{REF} data and clock differential-input receivers.
CSR, DCS	J2, H2	SSTL_18 input	Chip select inputs. Disables data outputs switching when both inputs are HIGH. [2]
D1 to D25	[1]	SSTL_18 input	Data inputs. Clocked in on the crossing of the rising edge of CK and the falling edge of CK.
DODT	[1]	SSTL_18 input	The outputs of this register will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control.
DCKE	[1]	SSTL_18 input	The outputs of this register will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control.
Q1 to Q25, Q1A to Q14A, Q1B to Q14B	[1]	1.8 V CMOS	The outputs that are suspended by DCS and CSR control. 3
QCS, QCSA, QCSB	[1]	1.8 V CMOS	Data outputs that will not be suspended by DCS and CSR control.
QODT, QODTA, QODTB	[1]	1.8 V CMOS	Data outputs that will not be suspended by DCS and CSR control.
QCKE, QCKEA, QCKEB	<u>[1]</u>	1.8 V CMOS	Data outputs that will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control.
n.c.	A2, D2, G1	-	Not connected. Ball present but no internal connection to the die.
d.n.u.	[1]	-	Do-not-use. Ball internally connected to the die which should be left open-circuit.

^[1] Depends on configuration. Refer to Figure 3, Figure 4, and Figure 5 for ball number.

[2] Configurations:

Data inputs = D2, D3, D5, D6, D8 to D25 when C0 = 0 and C1 = 0. Data inputs = D2, D3, D5, D6, D8 to D14 when C0 = 0 and C1 = 1. Data inputs = D1 to D6, D8 to D10, D12, D13 when C0 = 1 and C1 = 1.

[3] Configurations:

Product data sheet

Data outputs = Q2, Q3, Q5, Q6, Q8 to Q25 when C0 = 0 and C1 = 0. Data outputs = Q2, Q3, Q5, Q6, Q8 to Q14 when C0 = 0 and C1 = 1.

Data outputs = Q1 to Q6, Q8 to Q10, Q12, Q13 when C0 = 1 and C1 = 1.

6. Functional description

6.1 Function table

Table 3: Function table (each flip-flop)

		Inp	uts				Outputs [1	<u>l]</u>
RESET	DCS	CSR	СК	CK	Dn, DODT, DCKE	Qn	QCS	QODT, QCKE
Н	L	L	1	\downarrow	L	L	L	L
Н	L	L	1	\downarrow	Н	Н	L	Н
Н	L	L	L or H	L or H	Х	Q_0	Q_0	Q_0
Н	L	Н	1	\downarrow	L	L	L	L
Н	L	Н	1	\downarrow	Н	Н	L	Н
Н	L	Н	L or H	L or H	Х	Q_0	Q_0	Q_0
Н	Н	L	1	\downarrow	L	L	Н	L
Н	Н	L	1	\downarrow	Н	Н	Н	Н
Н	Н	L	L or H	L or H	Х	Q_0	Q_0	Q_0
Н	Н	Н	1	\downarrow	L	Q_0	Н	L
Н	Н	Н	1	\downarrow	Н	Q_0	Н	Н
Н	Н	Н	L or H	L or H	Х	Q_0	Q_0	Q_0
L	X or floating	L	L	L				

^[1] Q_0 is the previous state of the associated output.

H — HIGH voltage level

L - LOW voltage level

↓ — HIGH-to-LOW transition

↑ — LOW-to-HIGH transition

X — Don't care



7. Limiting values

Table 4: Limiting values [1]

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+2.5	V
VI	receiver input voltage		-0.5 [2]	+2.5 ^[3]	V
Vo	driver output voltage		-0.5 [2]	V _{DD} + 0.5 [3]	V
I _{IK}	input clamp current	$V_I < 0 \text{ V or } V_I > V_{DD}$	-	±50	mA
I _{OK}	output clamp current	$V_O < 0 \text{ V or } V_O > V_{DD}$	-	±50	mA
Io	continuous output current	$0 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{DD}}$	-	±50	mA
I _{CCC}	continuous current through each V _{DD} or GND pin		-	±100	mA
T _{stg}	storage temperature		-65	+150	°C

^[1] Stresses beyond those listed under 'absolute maximum ratings' may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under 'recommended operating conditions' is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Product data sheet

^[2] The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

^[3] This value is limited to 2.5 V maximum.



8. Recommended operating conditions

Table 5: Operating conditions

Table 3.	Operating conditions						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DD}	supply voltage			1.7	-	1.9	V
V_{REF}	reference voltage			$0.49 \times V_{DD}$	$0.50 \times V_{DD}$	$0.51 \times V_{DD}$	V
V_{TT}	termination voltage			$V_{\text{REF}}-40~\text{mV}$	V_{REF}	V_{REF} + 40 mV	V
V_{I}	input voltage			0	-	V_{DD}	V
$V_{\text{IH(AC)}}$	AC HIGH-level input voltage	$\frac{\text{data inputs (Dn),}}{\text{CSR}}$		V _{REF} + 250 mV	-	-	V
V _{IL(AC)}	AC LOW-level input voltage	data inputs (Dn), CSR		-	-	V _{REF} – 250 mV	V
$V_{IH(DC)}$	DC HIGH-level input voltage	data inputs (Dn), CSR		V _{REF} + 125 mV	-	-	V
$V_{IL(DC)}$	DC LOW-level input voltage	data inputs (Dn), CSR		-	-	V _{REF} – 125 mV	V
V_{IH}	HIGH-level input voltage	RESET, Cn	[1]	$0.65 \times V_{DD}$	-	V_{DD}	V
V_{IL}	LOW-level input voltage	RESET, Cn	[1]	-	-	$0.35 \times V_{DD}$	V
V_{ICR}	common mode input voltage range	CK, CK	[2]	0.675	-	1.125	V
V_{ID}	differential input voltage	CK, CK	[2]	600	-	-	mV
I _{OH}	HIGH-level output current			-	-	-8	mA
I _{OL}	LOW-level output current			-	-	8	mA
T _{amb}	operating ambient temperature in free air			0	-	+70	°C

^[1] The RESET and Cn inputs of the device must be held at valid logic levels (not floating) to ensure proper device operation.

^[2] The differential inputs must not be floating, unless $\overline{\text{RESET}}$ is LOW.

1.8 V configurable registered buffer for DDR2 RDIMM applications

9. Characteristics

Table 6: Characteristics

Recommended operating conditions, unless otherwise specified. Voltages are referenced to GND (ground = 0 V). $T_{amb} = 0 \,^{\circ}C$ to +70 $^{\circ}C$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level output voltage	$I_{OH} = -6 \text{ mA}; V_{DD} = 1.7 \text{ V}$	1.2	-	-	V
V _{OL}	LOW-level output voltage	$I_{OL} = 6 \text{ mA}; V_{DD} = 1.7 \text{ V}$	-	-	0.5	V
II	input current	all inputs; $V_I = V_{DD}$ or GND; $V_{DD} = 1.9 \text{ V}$	- 5	-	+5	μΑ
I _{DD}	static standby current	$\overline{\text{RESET}} = \text{GND}; I_{\text{O}} = 0 \text{ mA};$ $V_{\text{DD}} = 1.9 \text{ V}$	-	-	100	μΑ
	static operating current	$\overline{RESET} = V_{DD}; I_O = 0 \text{ mA};$ $V_{DD} = 1.9 \text{ V};$ $V_I = V_{IH(AC)} \text{ or } V_{IL(AC)}$	-	-	40	mA
I _{DDD}	dynamic operating current per MHz, clock only	$\overline{RESET} = V_{DD};$ $V_{I} = V_{IH(AC)} \text{ or } V_{IL(AC)}; \text{ CK and}$ $\overline{CK} \text{ switching at 50 \% duty cycle.}$ $I_{O} = 0 \text{ mA}; V_{DD} = 1.9 \text{ V}$	-	16	-	μΑ
	dynamic operating current per MHz, per each data input, 1:1 mode	$\overline{RESET} = V_{DD};$ $V_{I} = V_{IH(AC)} \text{ or } V_{IL(AC)}; \text{ CK and}$ $\overline{CK} \text{ switching at 50 \% duty cycle.}$ One data input switching at half clock frequency, 50 % duty cycle. $I_{O} = 0 \text{ mA}; V_{DD} = 1.9 \text{ V}$	-	11	-	μА
	dynamic operating current per MHz, per each data input, 1:2 mode	$\overline{RESET} = V_{DD};$ $V_{I} = V_{IH(AC)} \text{ or } V_{IL(AC)}; \text{ CK and}$ $\overline{CK} \text{ switching at 50 \% duty cycle.}$ One data input switching at half clock frequency, 50 % duty cycle. $I_{O} = 0 \text{ mA}; V_{DD} = 1.9 \text{ V}$	-	19	-	μА
C _i	input capacitance, data inputs, CSR	$V_I = V_{REF} \pm 250 \text{ mV};$ $V_{DD} = 1.8 \text{ V}$	2.5	-	3.5	pF
	input capacitance, CK and $\overline{\text{CK}}$	$V_{ICR} = 0.9 \text{ V}; V_{ID} = 600 \text{ mV}; V_{DD} = 1.8 \text{ V}$	2	-	3	pF
	input capacitance, RESET	$V_I = V_{DD}$ or GND; $V_{DD} = 1.8 \text{ V}$	2	-	4	pF

Product data sheet

1.8 V configurable registered buffer for DDR2 RDIMM applications

Table 7: Timing requirements

Recommended operating conditions; $V_{DD} = 1.8 \ V \pm 0.1 \ V$; $T_{amb} = 0 \ ^{\circ}C$ to +70 $^{\circ}C$; unless otherwise specified. See Figure 6 through Figure 11.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Symbol	raiailletei	Conditions	IVIII	Тур	IVIAX	Unit
f _{clock}	clock frequency		-	-	450	MHz
t _W	pulse duration, CK, $\overline{\text{CK}}$ HIGH or LOW		1	-	-	ns
t _{ACT}	differential inputs active time		[1][2]	-	10	ns
t _{INACT}	differential inputs inactive time		[1][3]	-	15	ns
t _{su}	set-up time	$\overline{\text{DCS}}$ before CK \uparrow , $\overline{\text{CK}} \downarrow$, $\overline{\text{CSR}}$ HIGH	0.7	-	-	ns
		$\overline{\text{DCS}}$ before CK \uparrow , $\overline{\text{CK}} \downarrow$, $\overline{\text{CSR}}$ LOW	0.5	-	-	ns
		$\overline{\text{CSR}}$, ODT, CKE, and data before CK \uparrow , $\overline{\text{CK}}$ \downarrow	0.5	-	-	ns
t _h	hold time	D $\overline{\text{CS}}$, $\overline{\text{CSR}}$, ODT, CKE, and data after CK \uparrow , $\overline{\text{CK}}$ \downarrow	0.5	-	-	ns

^[1] This parameter is not necessarily production tested.

Table 8: Switching characteristics

Recommended operating conditions; $V_{DD} = 1.8 \ V \pm 0.1 \ V$; $T_{amb} = 0 \ ^{\circ}C$ to $+70 \ ^{\circ}C$; Class I, $V_{REF} = V_{TT} = V_{DD} \times 0.5$ and $C_L = 10 \ pF$; unless otherwise specified. See Figure 6 through Figure 11.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f_{MAX}	maximum input clock frequency		450	-	-	MHz
t _{PDM}	propagation delay	CK and $\overline{\text{CK}}$ to output	[<u>1]</u> 1.41	-	1.8	ns
t _{PDMSS}	propagation delay, simultaneous switching	CK and $\overline{\text{CK}}$ to output	[1][2] -	-	2.0	ns
t _{PHL}	propagation delay	RESET to output	-	-	3	ns

^[1] Includes 350 ps of test-load transmission line delay.

Table 9: Output edge rates

Recommended operating conditions, unless otherwise specified. V_{DD} = 1.8 V \pm 0.1 V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV/dt_r	rising edge slew rate		1	-	4	V/ns
dV/dt_f	falling edge slew rate		1	-	4	V/ns
dV/dt_Δ	absolute difference between dV/dt_r and dV/dt_f		-	-	1	V/ns

^[2] Data inputs must be active below a minimum time of $t_{ACT(max)}$ after \overline{RESET} is taken HIGH.

^[3] Data and clock inputs must be held at valid levels (not floating) a minimum time of t_{INACT(max)} after RESET is taken LOW.

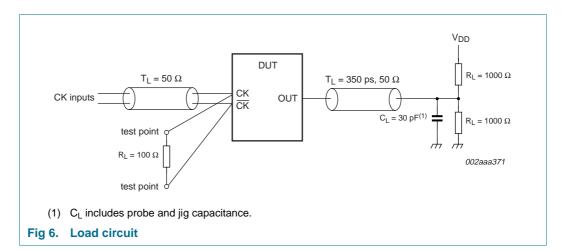
^[2] This parameter is not necessarily production tested.

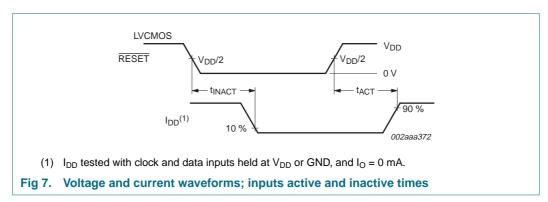
10. Test information

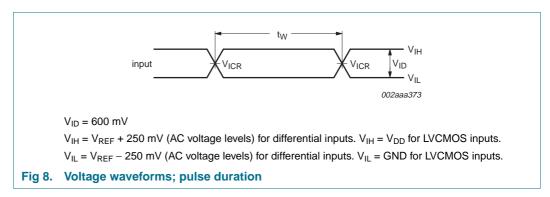
10.1 Test circuit

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; Z_0 = 50 Ω ; input slew rate = 1 V/ns \pm 20 %, unless otherwise specified.

The outputs are measured one at a time with one transition per measurement.







SSTU32864 **Philips Semiconductors**

1.8 V configurable registered buffer for DDR2 RDIMM applications

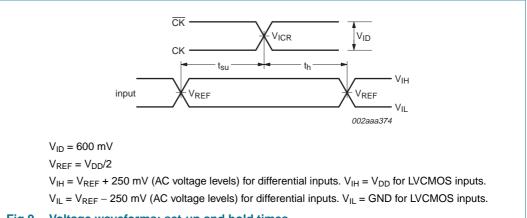


Fig 9. Voltage waveforms; set-up and hold times

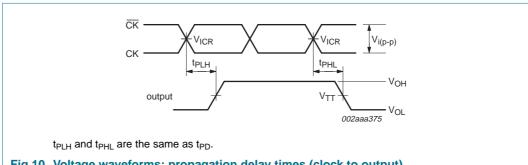
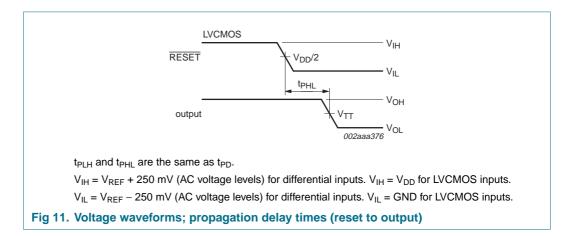


Fig 10. Voltage waveforms; propagation delay times (clock to output)

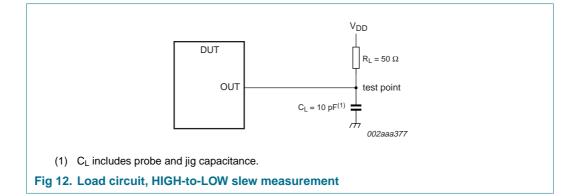


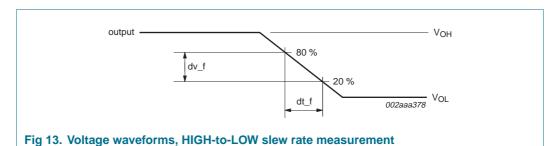
1.8 V configurable registered buffer for DDR2 RDIMM applications

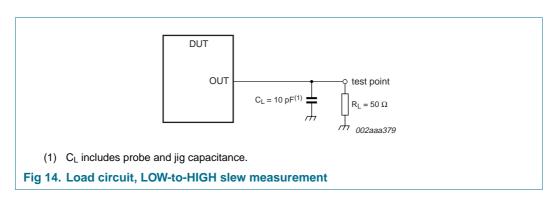
10.2 Output slew rate measurement

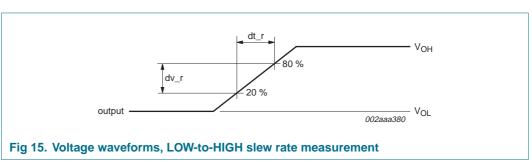
 $V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}.$

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; Z_0 = 50 Ω ; input slew rate = 1 V/ns \pm 20 %, unless otherwise specified.









11. Package outline

LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1

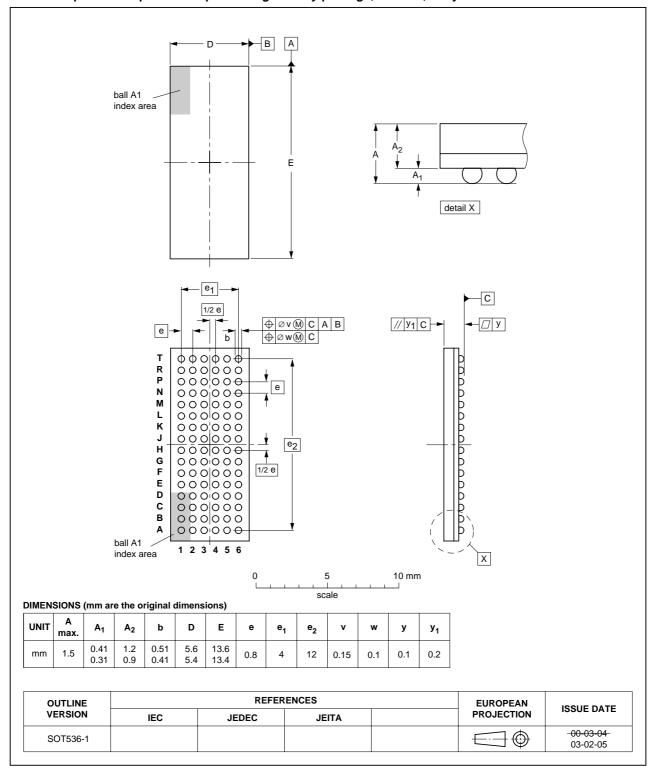


Fig 16. Package outline SOT536-1 (LFBGA96)

9397 750 14092

© Koninklijke Philips Electronics N.V. 2004. All rights reserved.



12. Soldering

12.1 Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *Data Handbook IC26; Integrated Circuit Packages* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

12.2 Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 seconds and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 °C to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferably be kept:

- below 225 °C (SnPb process) or below 245 °C (Pb-free process)
 - for all BGA, HTSSON..T and SSOP..T packages
 - for packages with a thickness ≥ 2.5 mm
 - for packages with a thickness < 2.5 mm and a volume ≥ 350 mm³ so called thick/large packages.
- below 240 °C (SnPb process) or below 260 °C (Pb-free process) for packages with a thickness < 2.5 mm and a volume < 350 mm³ so called small/thin packages.

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

12.3 Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;

9397 750 14092

1.8 V configurable registered buffer for DDR2 RDIMM applications

 smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 seconds to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

12.4 Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300\,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 seconds to 5 seconds between 270 °C and 320 °C.

12.5 Package related soldering information

Table 10: Suitability of surface mount IC packages for wave and reflow soldering methods

·					
Package [1]	Soldering method				
	Wave	Reflow [2]			
BGA, HTSSONT 3, LBGA, LFBGA, SQFP, SSOPT 3, TFBGA, VFBGA, XSON	not suitable	suitable			
DHVQFN, HBCC, HBGA, HLQFP, HSO, HSOP, HSQFP, HSSON, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable [4]	suitable			
PLCC [5], SO, SOJ	suitable	suitable			
LQFP, QFP, TQFP	not recommended [5] [6]	suitable			
SSOP, TSSOP, VSO, VSSOP	not recommended [7]	suitable			
CWQCCNL ^[8] , PMFP ^[9] , WQCCNL ^[8]	not suitable	not suitable			

For more detailed information on the BGA packages refer to the (LF)BGA Application Note (AN01026);
 order a copy from your Philips Semiconductors sales office.

^[2] All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods.

^[3] These transparent plastic packages are extremely sensitive to reflow soldering conditions and must on no account be processed through more than one soldering cycle or subjected to infrared reflow soldering with peak temperature exceeding 217 °C ± 10 °C measured in the atmosphere of the reflow oven. The package body peak temperature must be kept as low as possible.

1.8 V configurable registered buffer for DDR2 RDIMM applications

- [4] These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- [5] If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- [6] Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- [7] Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.
- [8] Image sensor packages in principle should not be soldered. They are mounted in sockets or delivered pre-mounted on flex foil. However, the image sensor package can be mounted by the client on a flex foil by using a hot bar soldering process. The appropriate soldering profile can be provided on request.
- [9] Hot bar soldering or manual soldering is suitable for PMFP packages.

13. Abbreviations

Table 11: Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Silicon
DDR	Double Data Rate
DIMM	Dual In-line Memory Module
JEDEC	Joint Electron Device Engineering Council
LFBGA	Low profile Fine-pitch Ball Grid Array
LVCMOS	Low Voltage Complementary Metal Oxide Silicon
PRR	Pulse Repetition Rate
RDIMM	Registered Dual In-line Memory Module
SSTL	Stub Series Terminated Logic

14. Revision history

Table 12: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes	
SSTU32864_2	20041022	Product data sheet	-	9397 750 14092	SSTU32864-01	
Modifications:	 The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors. 					
	 Data sheet status changed to 'Product data sheet'. 					
	Table 2 "P	in description"				
	– (new) Table note [1] added					
	pin (ball) numbers added					
	changed pin name 'DNU' to 'd.n.u.'					
	• Table 3 "Function table (each flip-flop)"					
	moved	to Section 6.1 on page	<u>7</u>			
	added	Table note 1 and its refe	erence at 'Outputs'			
	correct	ed column sub-heading	s under 'Outputs'			
	 <u>Table 4 "Limiting values [1]"</u>: Symbol V_i changed to V_I; Symbol V_o changed to V_O 					
	• Table 5 "Operating conditions":					
	 changed V_{IH} (for data inputs) to V_{IH(AC)} and V_{IH(DC)}; condition changed to 'data inputs (Dn)' 					
	– changed V_{IL} (for data inputs) to $V_{IL(AC)}$ and $V_{IL(DC)}$; condition changed to 'data inputs (Dn)'					
		ote split into 2 notes; re	ferences added.			
		haracteristics"				
	 changed I_{DDD} Parameter from "dynamic operating current" to "dynamic operating current per MHz"; change Unit from "μΑ/MHz" to "μΑ". 					
	• Table 7 "T	iming requirements":				
	– change	ed symbol f _{CLOCK} to f _{cloc}	k			
	– change	ed symbol t_{SU} to t_{su}				
	– change	ed symbol t _H to t _h				
	• Table 8 "Switching characteristics":					
	 changed t_{PDM} and t_{PDMSS} Conditions from 'clock to output' to 'CK and CK to output' 					
	 changed t_{PHL} Condition from 'reset to output' to 'RESET to output' 					
	 <u>Table 9 "Output edge rates"</u>: deleted Table note [1] 					
	Section 10	0.1 "Test circuit": titles fo	r <u>Figure 10</u> and <u>Figu</u>	re 11 modified.		
	Added See	ction 13 "Abbreviations"				
SSTU32864-01	20040712	Objective data	-	9397 750 13339	-	

19 of 21

15. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

- [1] Please consult the most recently issued data sheet before initiating or completing a design.
- [2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

16. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

17. Disclaimers

1.8 V configurable registered buffer for DDR2 RDIMM applications

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

18. Contact information

For additional information, please visit: http://www.semiconductors.philips.com
For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

Philips Semiconductors

SSTU32864

1.8 V configurable registered buffer for DDR2 RDIMM applications

19. Contents

1	General description
2	Features
3	Ordering information
4	Functional diagram 3
5	Pinning information 4
5.1	Pinning
5.2	Pin description 6
6	Functional description 7
6.1	Function table
7	Limiting values 8
8	Recommended operating conditions 9
9	Characteristics
10	Test information
10.1	Test circuit
10.2	Output slew rate measurement 14
11	Package outline 15
12	Soldering 16
12.1	Introduction to soldering surface mount
	packages 16
12.2	Reflow soldering
12.3	Wave soldering
12.4	Manual soldering
12.5	Package related soldering information 17
13	Abbreviations
14	Revision history
15	Data sheet status 20
16	Definitions
17	Disclaimers
18	Contact information 20

© Koninklijke Philips Electronics N.V. 2004

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 22 October 2004 Document number: 9397 750 14092

